

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TK3R3A06PL

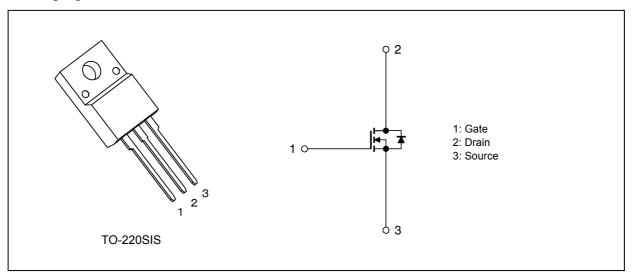
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 21 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 66 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 2.5 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode: V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_{D} = 0.7 mA)

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics | | | Symbol | Rating | Unit |
|--------------------------------|--------------------------|--------------------|-----------------------|------------|-------|
| Drain-source voltage | | | V_{DSS} | 60 | V |
| Gate-source voltage | | | V_{GSS} | ±20 | |
| Drain current (DC) | (T _c = 25 °C) | (Note 1) | I _D | 80 | Α |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I_D | 88 | Α |
| Drain current (pulsed) | (t = 100 μs) | (Note 1) | I_{DP} | 400 | Α |
| Power dissipation | (T _c = 25 °C) | | P_{D} | 42 | W |
| Single-pulse avalanche energy | | (Note 3) | E _{AS} | 76 | mJ |
| Single-pulse avalanche current | | (Note 3) | I _{AS} | 80 | Α |
| Channel temperature | | | T_ch | 175 | °C |
| Storage temperature | | | T_{stg} | -55 to 175 | °C |
| Isolation voltage (RMS) | (t = 1.0 s) | | V _{ISO(RMS)} | 2000 | V |
| Mounting torque | | | TOR | 0.6 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | |
|---------------------------------------|--------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | (T _c = 25 °C) | R _{th(ch-c)} | 3.57 | °C/W |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | R _{th(ch-a)} | 62.5 | |

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited by silicon chip capability.

Note 3: V_{DD} = 48 V, T_{ch} = 25 °C (initial), L = 9.2 μ H, I_{AS} = 80 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 60 | _ | _ | ٧ |
| Drain-source breakdown voltage (Note 4) | V _{(BR)DSX} | I _D = 10 mA, V _{GS} = -20 V | 45 | _ | _ | |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 0.7 mA | 1.5 | _ | 2.5 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 4.5 V, I _D = 34 A | _ | 3.3 | 4.9 | mΩ |
| | | V _{GS} = 10 V, I _D = 40 A | _ | 2.5 | 3.3 | |

Note 4: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz | _ | 5000 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | | 55 | _ | |
| Output capacitance | C _{oss} | | _ | 950 | _ | |
| Gate resistance | r _g | _ | _ | 1.5 | _ | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | | 7 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 25 | _ | |
| Switching time (fall time) | t _f | | _ | 16 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 66 | _ | |

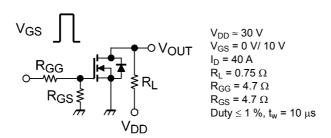


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | Qg | $V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$ | _ | 71 | _ | nC |
| gate-drain) | | $V_{DD} \approx 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 40 \text{ A}$ | _ | 35 | _ | |
| Gate-source charge 1 | Q _{gs1} | $V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$ | _ | 19 | _ | |
| Gate-drain charge | Q_{gd} | | _ | 13 | _ | |
| Gate switch charge | Q _{SW} | | _ | 21 | _ | |
| Output charge | Q _{oss} | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | _ | 66 | _ | |



6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 5) | I _{DRP} (t = 100 μs) | _ | 1 | ı | 400 | Α |
| Diode forward voltage | V_{DSF} | I _{DR} = 80 A, V _{GS} = 0 V | | | -1.5 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 20 A, V _{GS} = 0 V, | _ | 55 | _ | ns |
| Reverse recovery charge | Q _{rr} | -dI _{DR} /dt = 100 A/μs | | 72 | | nC |

Note 5: Ensure that the channel temperature does not exceed 175 °C.

7. Marking (Note)

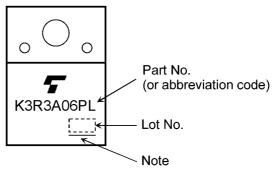


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

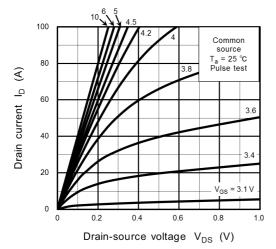


Fig. 8.1 I_D - V_{DS}

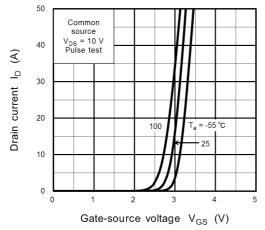


Fig. 8.3 I_D - V_{GS}

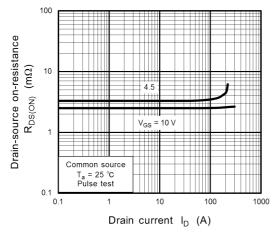


Fig. 8.5 R_{DS(ON)} - I_D

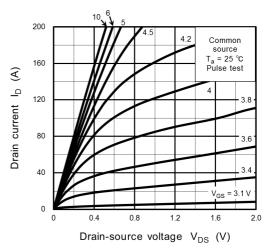


Fig. 8.2 I_D - V_{DS}

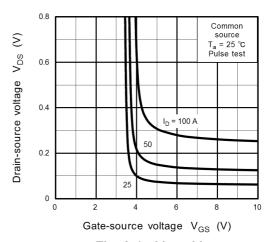


Fig. 8.4 VDS - VGS

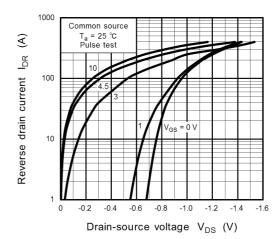


Fig. 8.6 I_{DR} - V_{DS}



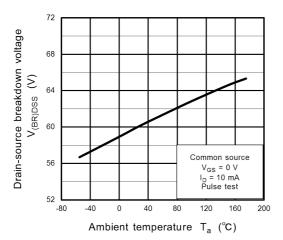


Fig. 8.7 V_{(BR)DSS} - T_a

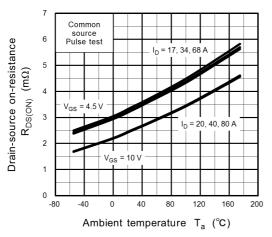


Fig. 8.9 R_{DS(ON)} - T_a

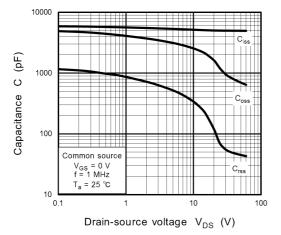


Fig. 8.11 Capacitance - V_{DS}

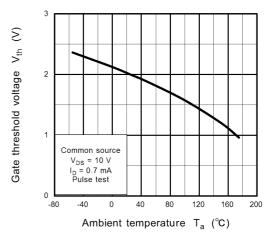


Fig. 8.8 V_{th} - T_a

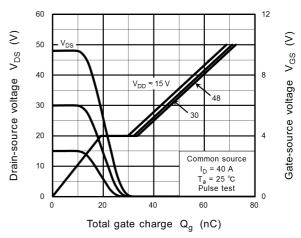


Fig. 8.10 Dynamic Input/Output Characteristics

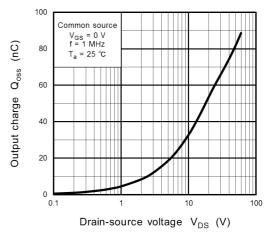


Fig. 8.12 Qoss - VDS



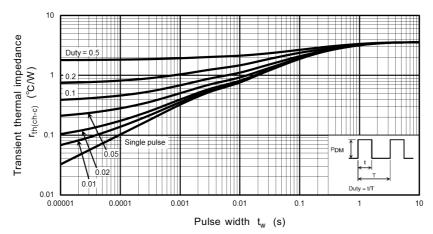
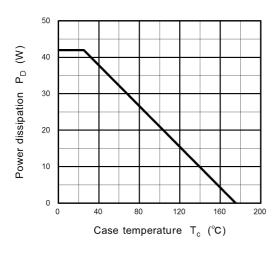


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)



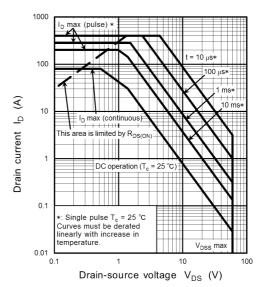


Fig. 8.14 P_D - T_c (Guaranteed Maximum)

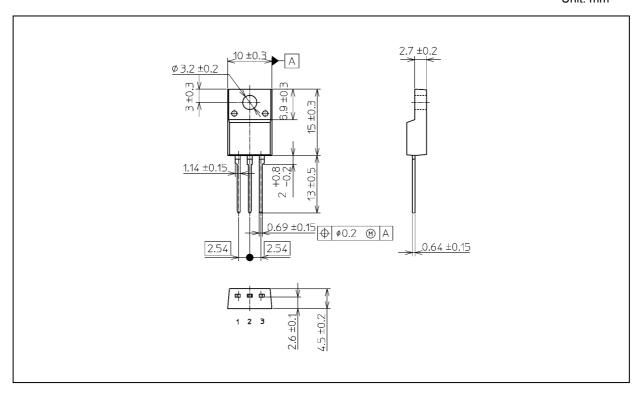
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.56 g (typ.)

| Package Name(s) |
|---------------------|
| TOSHIBA: 2-10U1S |
| Nickname: TO-220SIS |



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